

# PSMN004-36B

## N-channel TrenchMOS SiliconMAX logic level FET

Rev. 02 — 1 March 2010

Product data sheet

## 1. Product profile

### 1.1 General description

SiliconMAX logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

### 1.4 Quick reference data

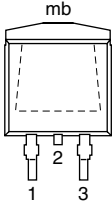
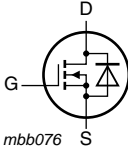
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	36	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V};$ see <a href="#">Figure 1</a> and <a href="#">3</a>	-	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	230	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}; I_D = 75\text{ A}; V_{DS} = 15\text{ V};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 11</a>	-	39	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	3.5	4	m $\Omega$
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	4	5	m $\Omega$



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;">SOT404 (D2PAK)</p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	D	drain <a href="#">[1]</a>		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2.

## 3. Ordering information

Table 3. Ordering information

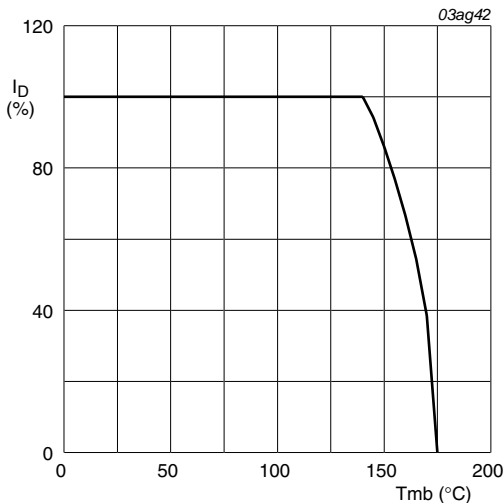
Type number	Package		Version
	Name	Description	
PSMN004-36B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

**Table 4. Limiting values**

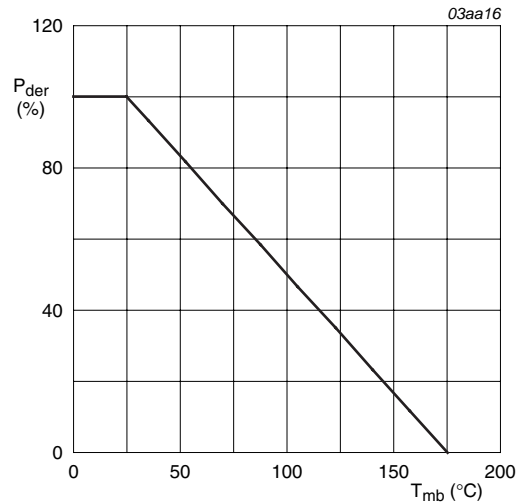
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	36	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	36	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a> V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a> and <a href="#">3</a>	-	75	A
I <sub>DM</sub>	peak drain current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	240	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	230	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; δ = 25 %; t <sub>p</sub> ≤ 50 μs; T <sub>j</sub> ≤ 150 °C	-20	20	V
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	75	A
I <sub>SM</sub>	peak source current	t <sub>p</sub> ≤ 10 μs; pulsed; T <sub>mb</sub> = 25 °C	-	240	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 75 A; V <sub>sup</sub> = 15 V; unclamped; t <sub>p</sub> = 0.1 ms; R <sub>GS</sub> = 50 Ω	-	120	mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> = 15 V; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω; unclamped	-	75	A



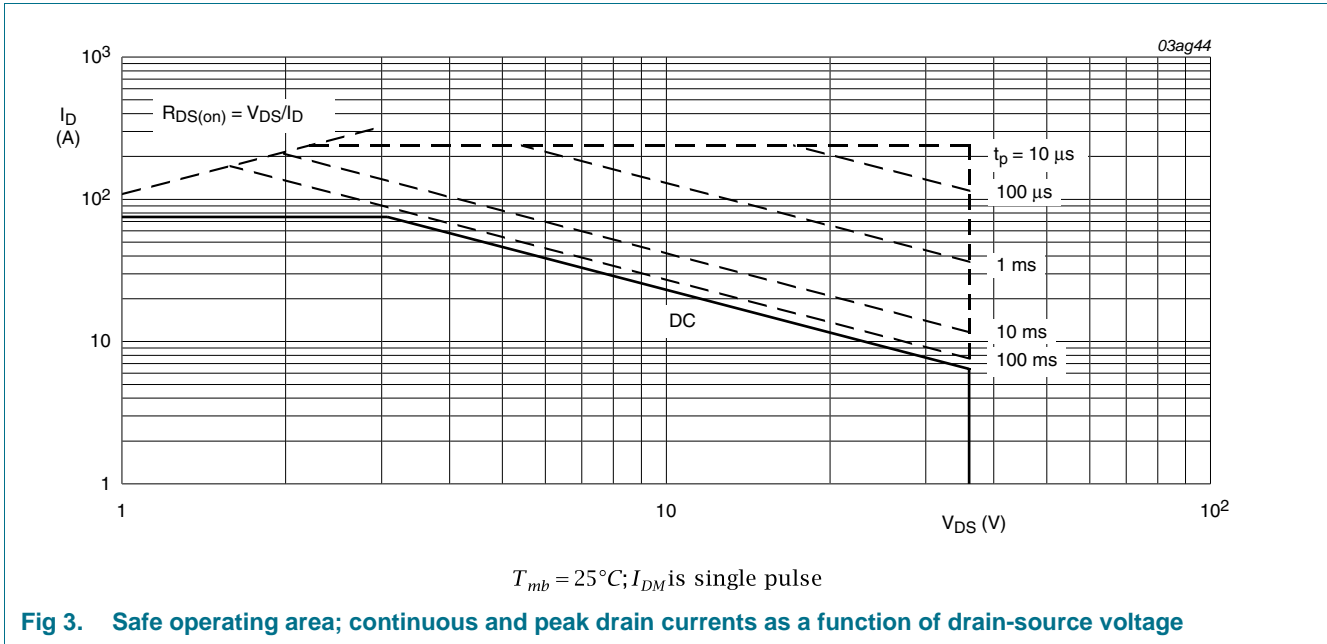
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

**Fig 1. Normalized continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

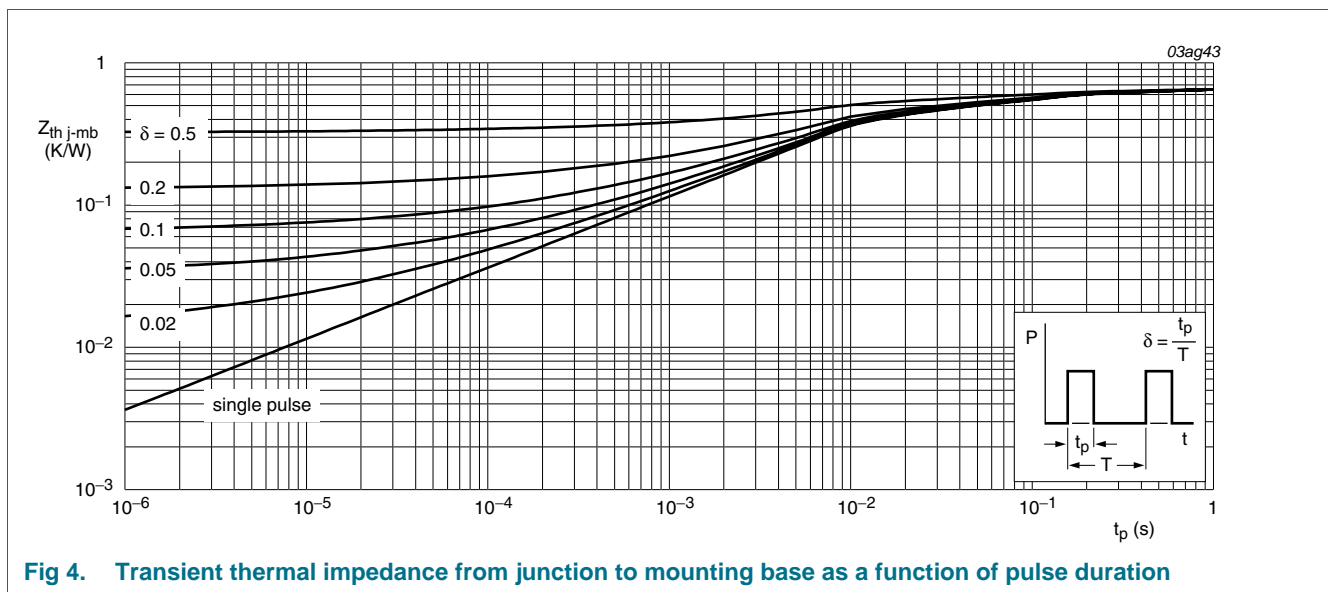
**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



### 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	-	50	K/W

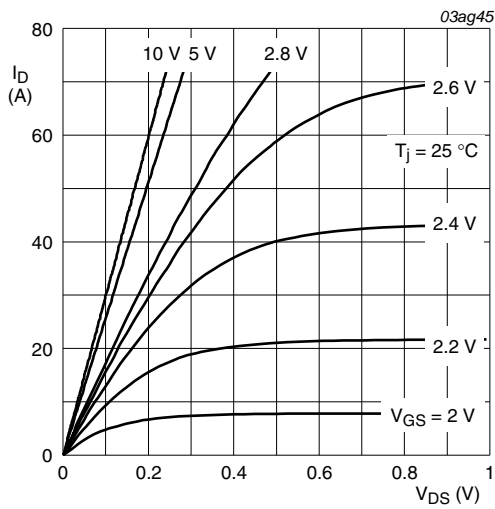


**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

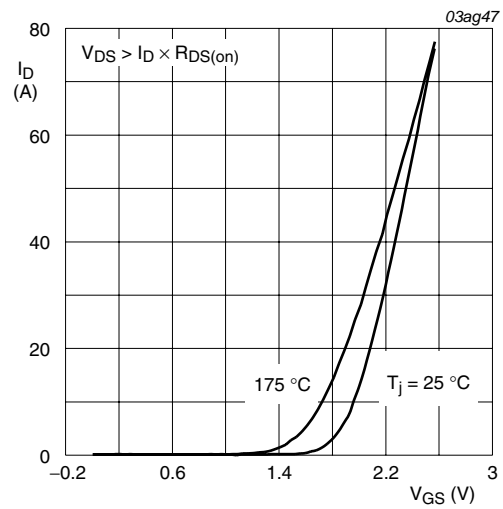
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	36	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	32	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 8</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 8</a>	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 8</a>	1	1.5	2	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	3.5	4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	-	9.25	m $\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	-	5.4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> and <a href="#">10</a>	-	4	5	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	-	97	-	nC
$Q_{GS}$	gate-source charge		-	20	-	nC
$Q_{GD}$	gate-drain charge		-	39	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	6000	-	pF
$C_{oss}$	output capacitance		-	1700	-	pF
$C_{rss}$	reverse transfer capacitance		-	1400	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	45	-	ns
$t_r$	rise time		-	220	-	ns
$t_{d(off)}$	turn-off delay time		-	435	-	ns
$t_f$	fall time		-	320	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 75 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	1.1	-	V
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	400	-	ns
$Q_r$	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1	-	$\mu\text{C}$



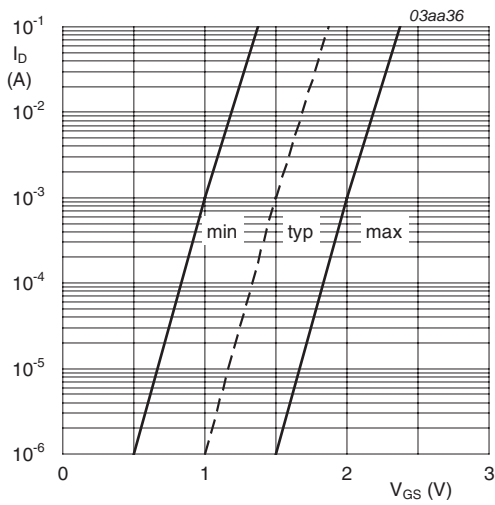
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



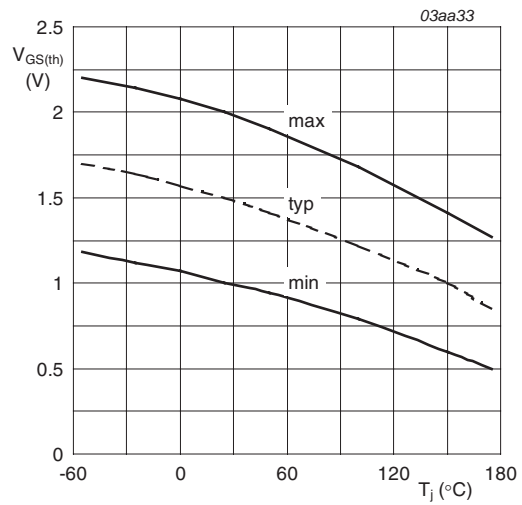
$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}$ ;  $V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



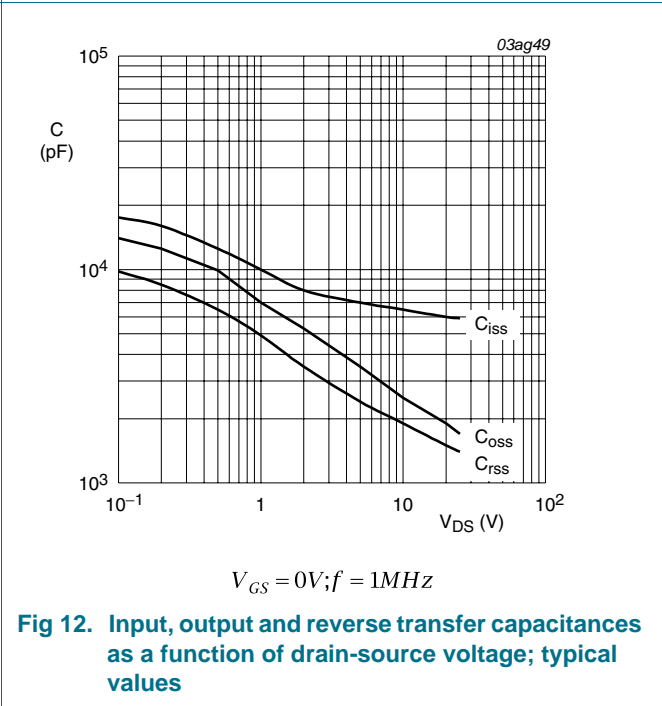
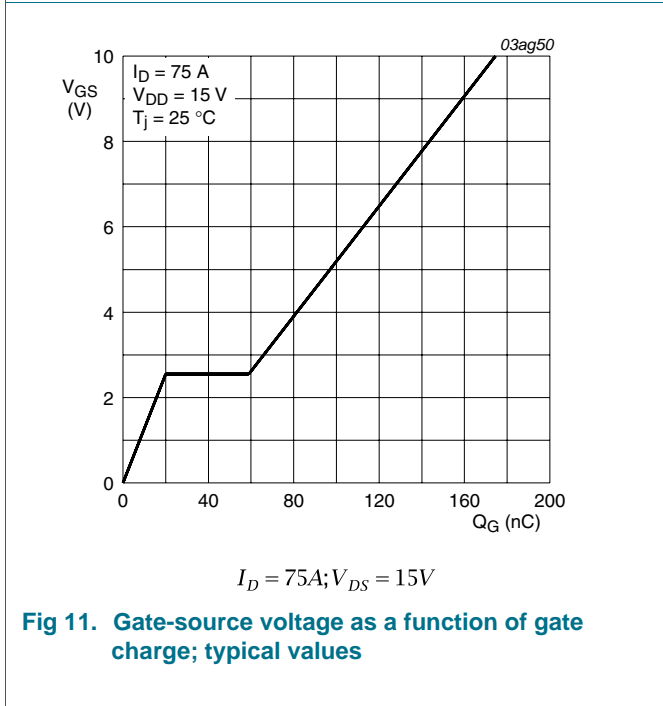
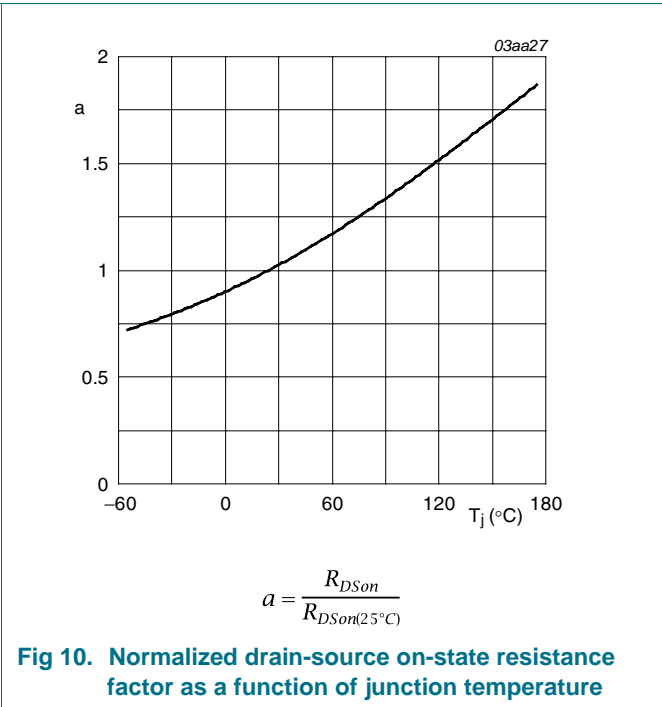
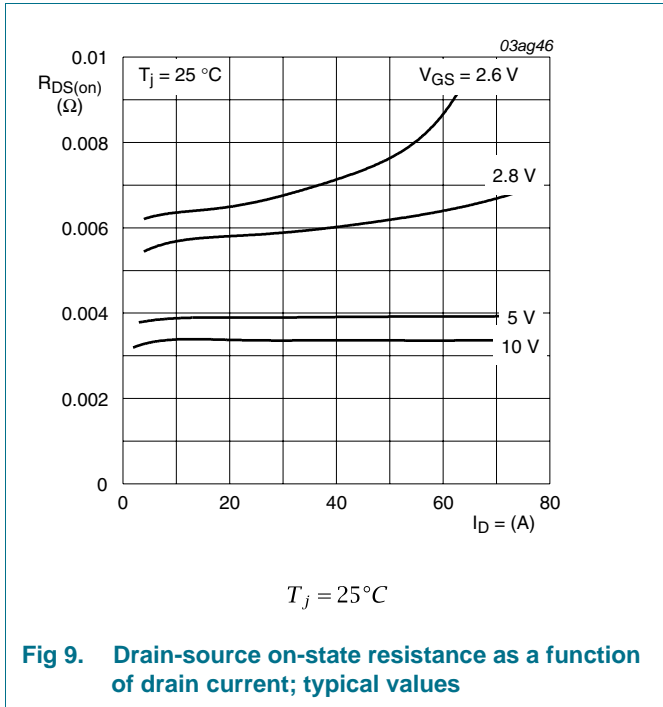
$T_j = 25^\circ\text{C}$ ;  $V_{DS} = V_{GS}$

Fig 7. Sub-threshold drain current as a function of gate-source voltage

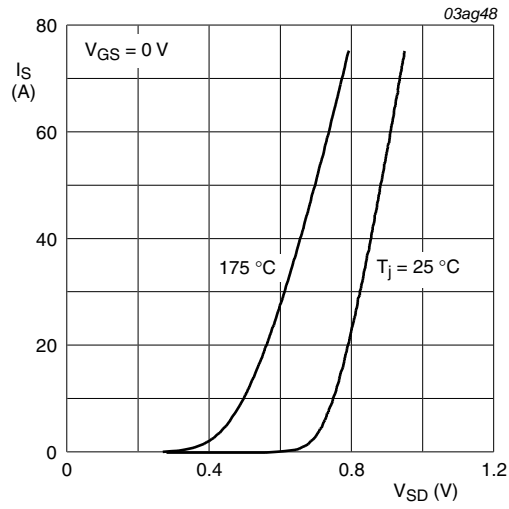


$I_D = 1\text{ mA}$ ;  $V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature







$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}; V_{GS} = 0\text{V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

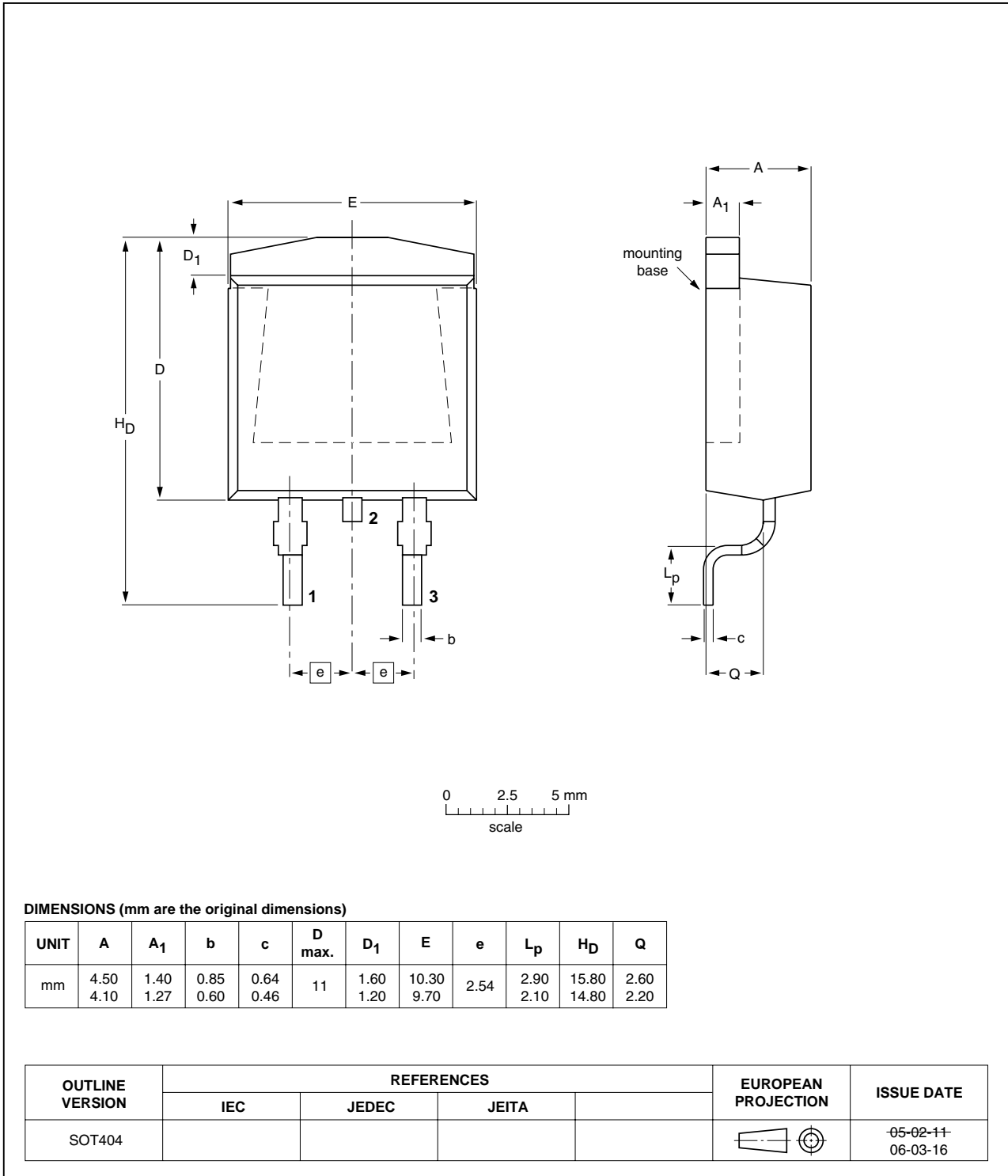


Fig 14. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN004-36B_2	20100301	Product data sheet	-	PSMN004_36P_36B-01
Modifications:				
			<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number PSMN004-36B_2 separated from data sheet PSMN004_36P_36B-01.</li></ul>	
PSMN004_36P_36B-01	20011119	Product data	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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